providing a plurality of electrodes and a plurality of high-power sources independently connected to each of said plurality of electrodes;

disposing a substrate on said plurality of electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

generating plasma; and

etching a material film on said substrate disposed on said plurality of electrodes,

wherein said plurality of electrodes are disposed so that an electric power applied to an entire surface of said substrate becomes uniform.

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27. A method of manufacturing a semiconductor device comprising:

providing a plurality of electrodes,

forming a material film on a substrate;

selectively forming a mask on said material film;

disposing said substrate on said plurality of electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to an electrode disposed below a central portion of said substrate and applying a second high-frequency power to electrodes disposed below corner portions of said substrate;

generating plasma; and

etching a material film on said substrate disposed on said plurality of electrodes.

28. A method of manufacturing a semiconductor device according to claim 27, wherein said semiconductor device is incorporated into an electronic device selected from the group consisting of a personal computer, a video camera, a mobile computer a goggle type display, a player, a digital camera, a front type projector, a rear type projector, a portable telephone a portable book, and a display.